



ZVP4525E6

250V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25℃
-250V	14Ω @ V _{GS} = -10V	-197mA
-250 V	18Ω @ V _{GS} = -3.5V	-175mA

Description

This 250V enhancement mode P-channel MOSFET provides users with a competitive specification. It offers efficient power handling capability, high impedance and is free from thermal runaway and thermally induced secondary breakdown. Applications benefiting from this device include a variety of Telecom and general high voltage circuits.

SOT89 and SOT223 versions are also available.

Applications

- Earth Recall and Dialing Switches
- Electronic Hook Switches
- High Voltage Power MOSFET Drivers
- Telecom Call Routers
- Solid State Relays

Features and Benefits

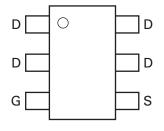
- High voltage
- Low on-resistance
- Fast switching speed
- Low gate drive
- Low threshold
- Complementary N-channel Type ZVN4525E6
- SOT23-6 package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

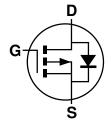
- Case: SOT26
- Case Material: Molded Plastic.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight 0.018 grams (Approximate)







Top View Pin-Out



Equivalent Circuit

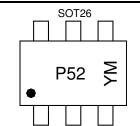
Ordering Information (Note 4)

Part Number	Case	Quantity per reel
ZVP4525E6TA	SOT26	3,000
ZVP4525E6TC	SOT26	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



P52 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: C = 2015) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Ī	Year	2015	2016	2017	2018	2019	2020	2021	2022
Ī	Code	С	D	E	F	G	Н		J

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

(Characteristic		Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-250	V
Gate-Source Voltage			V_{GS}	±40	V
Continuous Drain Current	101/	(Note 5)	I _D	-197	A
	$V_{GS} = 10V$	$T_A = +70 ^{\circ}\text{C} \text{ (Note 5)}$		-157	mA
Pulsed Drain Current	V _{GS} = 10V	(Note 7)	I _{DM}	-1	Α
Continuous Source Current	(Body Diode)		I _S	-0.75	Α
Pulsed Source Current (Bod	y Diode)		I _{SM}	-1	Α

Thermal Characteristics (@TA = +25 ℃, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 5)	D ₀	1.1	W
Linear Derating Factor	(Note 5)	P _D	8.8	mW/℃
Thermal Desistance Junction to Ambient	(Note 5)	В	113	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ hetaJA}$	68	3 - C/ VV
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

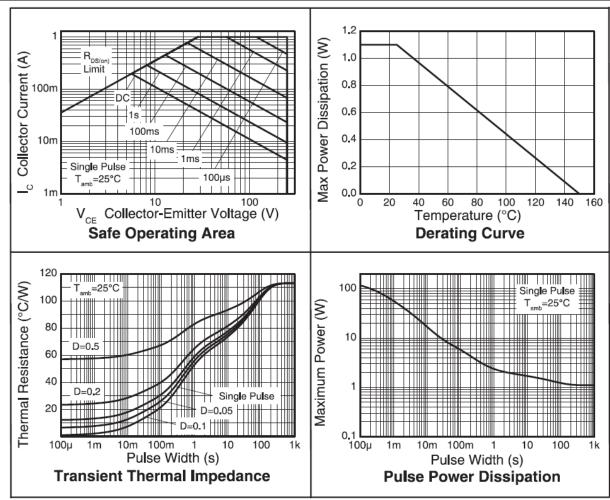
Notes:

- 5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 6. For a device surface mounted on FR4 PCB measured at $t \le 5$ secs.
- 7. Repetitive rating pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

NB High Voltage Applications

For high voltage applications, the appropriate industry sector guidelines should be considered with regard to voltage spacing between conductors.

Thermal Characteristics





Electrical Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

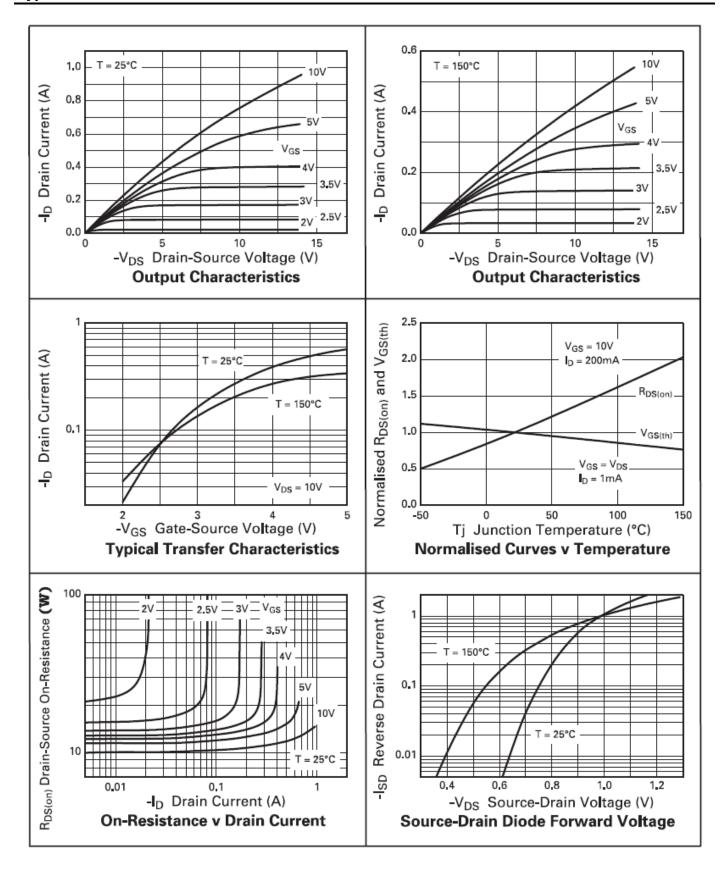
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS					•		
Drain-Source Breakdown Voltage	BV _{DSS}	-250	-285	_	V	$I_D = -1 \text{mA}, V_{GS} = 0 \text{V}$	
Zero Gate Voltage Drain Current	I _{DSS}	_	-30	-500	nA	V _{DS} = -250V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	±1	±100	nA	$V_{GS} = \pm 40V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(th)}$	-0.8	-1.5	-2.0	V	$I_D = -1 \text{mA}, \ V_{DS} = V_{GS}$	
Static Drain-Source On-Resistance (Note 8)	D		10	14	Ω	$V_{GS} = -10V, I_D = -200mA$	
Static Dialif-Source Off-nesistatice (Note 6)	R _{DS(ON)}	_	13	18	12	$V_{GS} = -3.5V, I_D = -100mA$	
Forward Transconductance (Notes 10)	g fs	80	200	_	mS	$V_{DS} = -10V, I_D = -0.15A$	
Diode Forward Voltage (Note 9)	V _{SD}	_	-0.86	-0.97	V	$I_S = -200 \text{mA}, V_{GS} = 0 \text{V},$ $T_J = +25 ^{\circ}\text{C}$	
DYNAMIC CHARACTERISTICS (Note 10)			L.		I.	•	
Input Capacitance	Ciss	_	73				
Output Capacitance	Coss		12.8	_	рF	$V_{DS} = -25V$, $V_{GS} = 0V$ f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	_	3.91	_			
Total Gate Charge (Note 9)	Qg	_	2.45	2.45		$V_{DS} = -25V$, $V_{GS} = -10V$,	
Gate-Source Charge (Note 9)	Q _{gs}	_	0.22	0.31	nC	$I_D = -200 \text{mA}$ (refer to	
Gate-Drain Charge (Note 9)	Q_{gd}	_	0.45	0.63		test circuit)	
Turn-On Delay Time (Note 9)	t _{D(on)}	_	1.53	_			
Turn-On Rise Time (Note 9)	t _r		3.78	_		$V_{DD} = -30V, V_{GS} = -10V$	
Turn-Off Delay Time (Note 9)	t _{D(off)}		17.5	_	ns	I_D = -200mA, R_G = 50 Ω (refer to test circuit)	
Turn-Off Fall Time (Note 9)	t _f		7.85			toot on out,	
Reverse Recovery Time	t _{rr}		205	290	ns	$I_F = -200 \text{mA}, \text{di/dt} = 100 \text{A/} \mu \text{s},$	
Reverse Recovery Charge	Q_{rr}	_	21	29	nC	T _J = +25 °C	

Notes:

^{8.} Measured under pulsed conditions. Width ≤ 300µs. Duty cycle ≤ 2%.
9. Switching characteristics are independent of operating junction temperatures.
10. For design aid only, not subject to production testing.

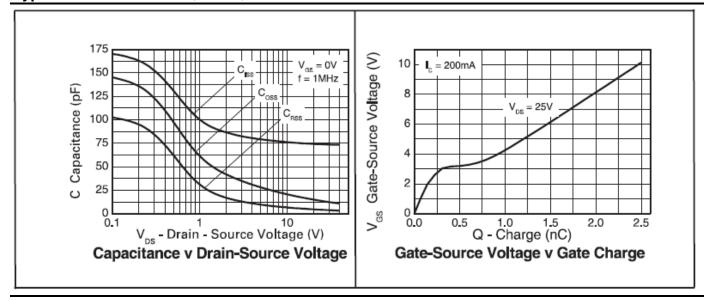


Typical Characteristics

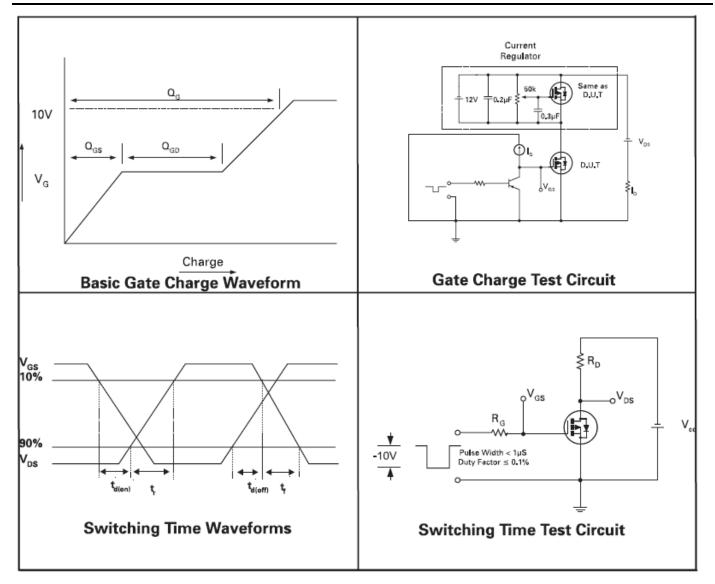




Typical Characteristics (continued)



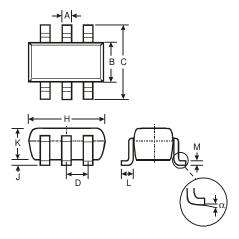
Test Circuits





Package Outline Dimensions

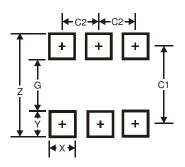
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT26								
Dim	Min	Max	Тур						
Α	0.35	0.50	0.38						
В	1.50	1.70	1.60						
С	2.70	3.00	2.80						
D	_	_	0.95						
Н	2.90	3.10	3.00						
J	0.013	0.10	0.05						
K	1.00	1.30	1.10						
L	0.35	0.55	0.40						
М	0.10	0.20	0.15						
α	0°	8°							
All D	All Dimensions in mm								

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Υ	0.80
C1	2.40
C2	0.95



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